

\* \* \* \* \* Welcome to STN International \* \* \* \* \*

<u>NEWS 1</u>		Web Page URLs for STN Seminar Schedule - N. America
<u>NEWS 2</u>		"Ask CAS" for self-help around the clock
<u>NEWS 3</u>	FEB 28	PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS 4</u>	FEB 28	BABS - Current-awareness alerts (SDIs) available
<u>NEWS 5</u>	MAR 02	GBFULL: New full-text patent database on STN
<u>NEWS 6</u>	MAR 03	REGISTRY/ZREGISTRY - Sequence annotations enhanced
<u>NEWS 7</u>	MAR 03	MEDLINE file segment of TOXCENTER reloaded
<u>NEWS 8</u>	MAR 22	KOREAPAT now updated monthly; patent information enhanced
<u>NEWS 9</u>	MAR 22	Original IDE display format returns to REGISTRY/ZREGISTRY
<u>NEWS 10</u>	MAR 22	PATDPASPC - New patent database available
<u>NEWS 11</u>	MAR 22	REGISTRY/ZREGISTRY enhanced with experimental property tags
<u>NEWS 12</u>	APR 04	EPFULL enhanced with additional patent information and new fields
<u>NEWS 13</u>	APR 04	EMBASE - Database reloaded and enhanced
<u>NEWS 14</u>	APR 18	New CAS Information Use Policies available online
<u>NEWS 15</u>	APR 25	Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAPLUS and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications.
<u>NEWS 16</u>	APR 28	Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAPLUS
<u>NEWS 17</u>	MAY 23	GBFULL enhanced with patent drawing images
<u>NEWS 18</u>	MAY 23	REGISTRY has been enhanced with source information from CHEMCATS
<u>NEWS 19</u>	JUN 06	The Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available
<u>NEWS 20</u>	JUN 13	RUSSIAPAT: New full-text patent database on STN
<u>NEWS 21</u>	JUN 13	FRFULL enhanced with patent drawing images
<u>NEWS 22</u>	JUN 27	MARPAT displays enhanced with expanded G-group definitions and text labels
<u>NEWS 23</u>	JUL 01	MEDICONF removed from STN
<u>NEWS 24</u>	JUL 07	STN Patent Forums to be held in July 2005
<u>NEWS 25</u>	JUL 13	SCISEARCH reloaded
<u>NEWS 26</u>	JUL 20	Powerful new interactive analysis and visualization software, STN AnaVist, now available
<u>NEWS EXPRESS</u>		JUNE 13 CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005
<u>NEWS HOURS</u>		STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>		General Internet Information
<u>NEWS LOGIN</u>		Welcome Banner and News Items
<u>NEWS PHONE</u>		Direct Dial and Telecommunication Network Access to STN
<u>NEWS WWW</u>		CAS World Wide Web Site (general information)

Enter NEWS followed by the item number or name to see news on that specific topic.

All use of STN is subject to the provisions of the STN Customer agreement. Please note that this agreement limits use to scientific research. Use for software development or design or implementation of commercial gateways or other similar uses is prohibited and may result in loss of user privileges and other penalties.

\* \* \* \* \* STN Columbus \* \* \* \* \*

\*ENCOMPLIT - EnCompass Literature File 1964-present (Supporters)  
 \*ENCOMPLIT2 - EnCompass Literature File 1964-Present (Non-Supporters)  
 \*ENCOMPPAT - EnCompass Patent File 1964-present (Supporters)  
 \*ENCOMPPAT2 - EnCompass Patent File 1964-Present (Non-Supporters)

\* The files listed above are temporarily unavailable.

FILE 'HOME' ENTERED AT 09:29:59 ON 27 JUL 2005

=> file inspec

COST IN U.S. DOLLARS

SINCE FILE  
ENTRY TOTAL  
SESSION

FULL ESTIMATED COST

0.21 0.21

FILE 'INSPEC' ENTERED AT 09:30:10 ON 27 JUL 2005

Compiled and produced by the IEE in association with FIZ KARLSRUHE

COPYRIGHT 2005 (c) INSTITUTION OF ELECTRICAL ENGINEERS (IEE)

FILE LAST UPDATED: 25 JUL 2005 <20050725/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
THE BASIC INDEX >>>

=> s copper interdiffusion

145933 COPPER

14603 INTERDIFFUSION

L1 1 COPPER INTERDIFFUSION

(COPPER(W) INTERDIFFUSION)

=> d 11

L1 ANSWER 1 OF 1 INSPEC (C) 2005 IEE on STN

Full Text

AN 1991:3969613 INSPEC DN A91122523

TI The effect of microstructure on the magnetic behavior of epitaxial cobalt layers.

AU Mankey, G.J.; Kief, M.T.; Willis, R.F. (Dept. of Phys., Pennsylvania State Univ., University Park, PA, USA)

SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1991) vol.9, no.3, pt.2, p.1595-8. 16 refs.

Price: CCCC 0734-2101/91/031595-04\$01.00

CODEN: JVTAD6 ISSN: 0734-2101

Conference: 37th National Symposium of the American Vacuum Society.

Toronto, Ont., Canada, 8-12 Oct 1990

DT Conference Article; Journal

TC Experimental

CY United States

LA English

=>

\* \* \* \* \* Welcome to STN International \* \* \* \* \*

<u>NEWS 1</u>		Web Page URLs for STN Seminar Schedule - N. America
<u>NEWS 2</u>		"Ask CAS" for self-help around the clock
<u>NEWS 3</u>	FEB 28	PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS 4</u>	FEB 28	BABS - Current-awareness alerts (SDIs) available
<u>NEWS 5</u>	MAR 02	GBFULL: New full-text patent database on STN
<u>NEWS 6</u>	MAR 03	REGISTRY/ZREGISTRY - Sequence annotations enhanced
<u>NEWS 7</u>	MAR 03	MEDLINE file segment of TOXCENTER reloaded
<u>NEWS 8</u>	MAR 22	KOREAPAT now updated monthly; patent information enhanced
<u>NEWS 9</u>	MAR 22	Original IDE display format returns to REGISTRY/ZREGISTRY
<u>NEWS 10</u>	MAR 22	PATDPASPC - New patent database available
<u>NEWS 11</u>	MAR 22	REGISTRY/ZREGISTRY enhanced with experimental property tags
<u>NEWS 12</u>	APR 04	EPFULL enhanced with additional patent information and new fields
<u>NEWS 13</u>	APR 04	EMBASE - Database reloaded and enhanced
<u>NEWS 14</u>	APR 18	New CAS Information Use Policies available online
<u>NEWS 15</u>	APR 25	Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAPLUS and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications.
<u>NEWS 16</u>	APR 28	Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAPLUS
<u>NEWS 17</u>	MAY 23	GBFULL enhanced with patent drawing images
<u>NEWS 18</u>	MAY 23	REGISTRY has been enhanced with source information from CHEMCATS
<u>NEWS 19</u>	JUN 06	The Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available
<u>NEWS 20</u>	JUN 13	RUSSIAPAT: New full-text patent database on STN
<u>NEWS 21</u>	JUN 13	FRFULL enhanced with patent drawing images
<u>NEWS 22</u>	JUN 27	MARPAT displays enhanced with expanded G-group definitions and text labels
<u>NEWS 23</u>	JUL 01	MEDICONF removed from STN
<u>NEWS 24</u>	JUL 07	STN Patent Forums to be held in July 2005
<u>NEWS 25</u>	JUL 13	SCISEARCH reloaded
<u>NEWS 26</u>	JUL 20	Powerful new interactive analysis and visualization software, STN AnaVist, now available
<u>NEWS EXPRESS</u>	JUNE 13	CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005
<u>NEWS HOURS</u>		STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>		General Internet Information
<u>NEWS LOGIN</u>		Welcome Banner and News Items
<u>NEWS PHONE</u>		Direct Dial and Telecommunication Network Access to STN
<u>NEWS WWW</u>		CAS World Wide Web Site (general information)

Enter NEWS followed by the item number or name to see news on that specific topic.

All use of STN is subject to the provisions of the STN Customer agreement. Please note that this agreement limits use to scientific research. Use for software development or design or implementation of commercial gateways or other similar uses is prohibited and may result in loss of user privileges and other penalties.

\* \* \* \* \* STN Columbus \* \* \* \* \*

\*ENCOMPLIT - EnCompass Literature File 1964-present (Supporters)  
 \*ENCOMPLIT2 - EnCompass Literature File 1964-Present (Non-Supporters)  
 \*ENCOMPPAT - EnCompass Patent File 1964-present (Supporters)  
 \*ENCOMPPAT2 - EnCompass Patent File 1964-Present (Non-Supporters)

\* The files listed above are temporarily unavailable.

FILE 'HOME' ENTERED AT 09:29:59 ON 27 JUL 2005

=> file inspec

COST IN U.S. DOLLARS	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'INSPEC' ENTERED AT 09:30:10 ON 27 JUL 2005

Compiled and produced by the IEE in association with FIZ KARLSRUHE  
 COPYRIGHT 2005 (c) INSTITUTION OF ELECTRICAL ENGINEERS (IEE)

FILE LAST UPDATED: 25 JUL 2005 <20050725/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
 THE BASIC INDEX >>>

=> s copper interdiffusion

145933 COPPER

14603 INTERDIFFUSION

L1 1 COPPER INTERDIFFUSION  
 (COPPER(W) INTERDIFFUSION)

=> d 11

L1 ANSWER 1 OF 1 INSPEC (C) 2005 IEE on STN

Full Text

AN 1991:3969613 INSPEC DN A91122523

TI The effect of microstructure on the magnetic behavior of epitaxial cobalt layers.

AU Mankey, G.J.; Kief, M.T.; Willis, R.F. (Dept. of Phys., Pennsylvania State Univ., University Park, PA, USA)

SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1991) vol.9, no.3, pt.2, p.1595-8. 16 refs.

Price: CCCC 0734-2101/91/031595-04\$01.00

CODEN: JVTAD6 ISSN: 0734-2101

Conference: 37th National Symposium of the American Vacuum Society. Toronto, Ont., Canada, 8-12 Oct 1990

DT Conference Article; Journal

TC Experimental

CY United States

LA English

=> s copper

L2 145933 COPPER

=> s diffusion

L3 212144 DIFFUSION

=> s tin or titanium nitride

55702 TIN  
 86985 TITANIUM  
 31457 NITRIDE  
 2283 TITANIUM NITRIDE  
           (TITANIUM(W)NITRIDE)  
 L4       56000 TIN OR TITANIUM NITRIDE

=> s 12 and 13 and 14  
 L5       1025 L2 AND L3 AND L4

=> s 13 same 12  
 MISSING OPERATOR L3 SAME  
 The search profile that was entered contains terms or  
 nested terms that are not separated by a logical operator.

=> s copper diffusion  
       145933 COPPER  
       212144 DIFFUSION  
 L6       431 COPPER DIFFUSION  
           (COPPER(W)DIFFUSION)

=> s plug  
 L7       9515 PLUG

=> s via  
 L8       190361 VIA

=> s 16 and 17  
 L9       1 L6 AND L7

=> d 19

L9   ANSWER 1 OF 1   INSPEC   (C) 2005 IEE on STN

**Full Text**

AN   1999:6234126   INSPEC       DN   B1999-06-2550F-011  
 TI   IMP Ta/Cu seed layer technology for high-aspect-ratio via fill by  
       electroplating, and its application to multilevel single damascene copper  
       interconnects.  
 AU   Hashim, I.; Pavate, V.; Peijun Ding; Chin, B. (Appl. Mater. Inc., Santa  
       Clara, CA, USA); Brown, D.; Nogami, T.  
 SO   Proceedings of the SPIE - The International Society for Optical  
       Engineering (1998) vol.3508, p.58-64. 9 refs.  
       Published by: SPIE-Int. Soc. Opt. Eng  
       Price: CCCC 0277-786X/98/\$10.00  
       CODEN: PSISDG   ISSN: 0277-786X  
       SICI: 0277-786X(1998)3508L:58:SLTH;1-K  
       Conference: Multilevel Interconnect Technology II. Santa Clara, CA, USA,  
       23-24 Sept 1998  
       Sponsor(s): SPIE  
 DT   Conference Article; Journal  
 TC   Experimental  
 CY   United States  
 LA   English

=> s 16 and 18  
 L10       24 L6 AND L8

=> d 110 1-24

L10 ANSWER 1 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:8345747 INSPEC DN A2005-10-8160B-037; B2005-05-2530F-018  
 TI Oxidation mechanism of ionic transport of copper in SiO<sub>2</sub> dielectrics.  
 AU Willis, B.G. (Dept. of Chem. Eng., Delaware Univ., Newark, DE, USA); Lang, D.V.  
 SO Thin Solid Films (22 Nov. 2004) vol.467, p.284-93. 29 refs.  
 Published by: Elsevier  
 Price: CCCC 0040-6090/2004/\$30.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(20041122)467L:284:OMIT;1-3  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L10 ANSWER 2 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7997827 INSPEC DN A2004-15-8235-002  
 TI Surface modification of SiLK(R) by graft copolymerization with 4-vinylpyridine for reduction in **copper diffusion**.  
 AU Zhu, Y.Q.; Kang, E.T.; Neoh, K.G. (Dept. of Chem. & Environ. Eng., Nat. Univ. of Singapore, Singapore); Chan, L.; Lai, D.M.Y.; Huan, A.C.H.  
 SO Applied Surface Science (30 March 2004) vol.225, no.1-4, p.144-55. 42 refs.  
 Published by: Elsevier  
 Price: CCCC 0169-4332/2004/\$30.00  
 CODEN: ASUSEE ISSN: 0169-4332  
 SICI: 0169-4332(20040330)225:1/4L:144:SMMSG;1-C  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L10 ANSWER 3 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7883001 INSPEC DN B2004-04-2550F-026  
 TI The application of ALD WNxCy as a **copper diffusion** barrier.  
 AU Smith, S. (Philips Semicond., XXX, France); Book, G.; Li, W.M.; Sun, Y.M.; Gillespie, P.; Tuominen, M.; Pfeifer, K.  
 SO Proceedings of the IEEE 2003 International Interconnect Technology Conference (Cat. No.03TH8695)  
 Piscataway, NJ, USA: IEEE, 2003. p.135-7 of 271 pp. 6 refs.  
 Conference: Burlingame, CA, USA, 2-4 June 2003  
 Sponsor(s): IEEE Electron Devices Soc  
 Price: CCCC 0 7803 7797 4/2003/\$17.00  
 ISBN: 0-7803-7797-4  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 4 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2003:7792364 INSPEC DN B2004-01-2550F-010

TI Electromigration improvement with PDL TiN(Si) barrier in copper dual damascene structures.

AU Alers, G.B.; Vijayendran, A. (Novellus Syst., San Jose, CA, USA); Gillespie, P.; Chen, L.; Cox, H.; Lam, K.; Augur, R.; Shannon, K.; Pfeifer, S.; Danek, M.

SO 2003 IEEE International Reliability Physics Symposium Proceedings 41st Annual (Cat. No.03CH37400)  
Piscataway, NJ, USA: IEEE, 2003. p.151-5 of 645 pp. 7 refs.  
Conference: Dallas, TX, USA, 30 March-4 April 2003  
Sponsor(s): IEEE Electron Devices Soc.; IEEE Reliability Soc  
Price: CCCC 0-7803-7649-8/03/\$17.00  
ISBN: 0-7803-7649-8

DT Conference Article  
TC Experimental  
CY United States  
LA English

L10 ANSWER 5 OF 24 INSPEC (C) 2005 IEE on STN



AN 2003:7728857 INSPEC DN A2003-20-6860-018; B2003-10-2550F-035

TI Copper grain boundary diffusion in electroless deposited cobalt based films and its influence on diffusion barrier integrity for copper metallization.

AU Kohn, A.; Eizenberg, M. (Dept. of Mater. Eng., Technion-Israel Inst. of Technol., Haifa, Israel); Shacham-Diamand, Y.

SO Journal of Applied Physics (1 Sept. 2003) vol.94, no.5, p.3015-24. 31 refs.  
Doc. No.: S0021-8979(03)04318-4  
Published by: AIP  
Price: CCCC 0021-8979/2003/94(5)/3015(10)/\$20.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(20030901)94:5L:3015:CGBD;1-7

DT Journal  
TC Experimental  
CY United States  
LA English

L10 ANSWER 6 OF 24 INSPEC (C) 2005 IEE on STN



AN 2003:7594518 INSPEC DN A2003-11-7920N-036; B2003-05-2550B-043

TI SIMS depth profile of copper in low-k dielectrics under electron irradiation for charge compensation.

AU Yamada, K.; Fujiyama, N.; Sameshima, J.; Kamoto, R.; Karen, A. (Toray Res. Center Inc., Shiga, Japan)

SO Applied Surface Science (15 Jan. 2003) vol.203-204, p.512-15. 3 refs.  
Doc. No.: S0169-4332(02)00767-5  
Published by: Elsevier  
Price: CCCC 0169-4332/03/\$30.00  
CODEN: ASUSEE ISSN: 0169-4332  
SICI: 0169-4332(20030115)203/204L:512:SDPC;1-2  
Conference: Thirteenth International Conference on Secondary Ion Mass Spectrometry and Related Topics. Nara, Japan, 11-16 Nov 2001  
Sponsor(s): Microbeam Analysis 141 Committee of Japan Soc. Promotion of Sci.; Commemorative Assoc. Japan World Exposition (1970)

DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

L10 ANSWER 7 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2003:7506552 INSPEC DN A2003-04-8120S-011  
 TI Synthesis of polyimides containing triazole to improve their adhesion to copper substrate.  
 AU Jeonghoon Seo; Jeonghoon Kang; Kilwon Cho; Chan Eon Park (Polymer Res. Inst., Pohang Univ. of Sci. & Technol. (POSTECH), South Korea)  
 SO Journal of Adhesion Science and Technology (2002) vol.16, no.13, p.1839-51. 18 refs.  
 Published by: VSP  
 CODEN: JATEE8 ISSN: 0169-4243  
 SICI: 0169-4243(2002)16:13L.1839:SPCT;1-8  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L10 ANSWER 8 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7480317 INSPEC DN B2003-01-2550F-026  
 TI Reliability of copper dual damascene influenced by pre-clean.  
 AU Tokei, Zs.; Lanckmans, F.; Van den bosch, G.; Van Hove, M.; Maex, K.; Bender, H. (IMEC, Leuven, Belgium); Hens, S.; Van Landuyt, J.  
 SO Proceedings of the 9th International Symposium on the Physical and Failure Analysis of Integrated Circuits (Cat. No.02TH8614)  
 Piscataway, NJ, USA: IEEE, 2002. p.118-23 of 258 pp. 6 refs.  
 Conference: Singapore, 8-12 July 2002  
 Price: CCCC 0-7803-7416-9/02/\$17.00  
 ISBN: 0-7803-7416-9  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L10 ANSWER 9 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7426102 INSPEC DN A2002-23-8115H-032; B2002-12-2550F-068  
 TI Physical and electrical characterization of ALD TiN used as a **copper diffusion** barrier in 0.25  $\mu$ m, dual damascene backend structures.  
 AU Smith, S.R. (Philips Semicond. Assignees, Int. Sematech, Austin, TX, USA); Elers, K.E.; Jacobs, T.; Blaschke, V.; Pfeifer, K.  
 SO Advanced Metallization Conference 2001 (AMC 2001). Proceedings of the Conference  
 Editor(s): McKerrow, A.J.; Shacham-Diamand, Y.; Zaima, S.; Ohba, T.  
 Warrendale, PA, USA: Mater. Res. Soc, 2001. p.593-5 of xxii+719 pp. 3 refs.  
 Conference: Montreal, Que., Canada, 29-31 Oct 2001  
 ISBN: 1-55899-670-2  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 10 OF 24 INSPEC (C) 2005 IEE on STN

Full Text



AN 2001:7078401 INSPEC DN A2001-23-6630J-009; B2001-12-2520C-012  
 TI Study of copper silicide retardation effects on **copper diffusion** in silicon.  
 AU Lee, C.S.; Gong, H. (Dept. of Mater. Sci., Nat. Univ. of Singapore, Kent Ridge, Singapore); Liu, R.; Wee, A.T.S.; Cha, C.L.; See, A.; Chan, L.  
 SO Journal of Applied Physics (15 Oct. 2001) vol.90, no.8, p.3822-4. 7 refs.  
 Doc. No.: S0021-8979(01)04505-4  
 Published by: AIP  
 Price: CCCC 0021-8979/2001/90(8)/3822(3)/\$18.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 SICI: 0021-8979(20011015)90:8L:3822:SCSR;1-Y  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 11 OF 24 INSPEC (C) 2005 IEE on STN



AN 2001:7074383 INSPEC DN B2001-12-2550F-039  
 TI Properties of ion-implanted low-k organic SOG.  
 AU Matsubara, N.; Mizuhara, H.; Yamashita, K.M.K.; Goto, T.; Inoue, Y.; Ibaraki, A. (Microelectron. Res. Center, Sanyo Electr. Co. Ltd., Gifu, Japan)  
 SO Proceedings of the IEEE 2001 International Interconnect Technology Conference (Cat. No.01EX461)  
 Piscataway, NJ, USA: IEEE, 2001. p.165-7 of iii+300 pp. 5 refs.  
 Conference: Burlingame, CA, USA, 4-6 June 2001  
 Sponsor(s): IEEE Electron Devices Soc  
 Price: CCCC 0 7803 6678 6/2001/\$10.00  
 ISBN: 0-7803-6678-6  
 DT Conference Article  
 TC Practical; Experimental  
 CY United States  
 LA English

L10 ANSWER 12 OF 24 INSPEC (C) 2005 IEE on STN



AN 2001:6895909 INSPEC DN B2001-05-2550F-037  
 TI Damascene test structures for the evaluation of barrier layer performance against **copper diffusion**.  
 AU Motte, P. (STMicroelectronics, Crolles, France); Swaanen, M.; Torres, J.; Gilet, J.M.; Wyborn, G.  
 SO Microelectronic Engineering (March 2001) vol.55, no.1-4, p.291-6. 2 refs.  
 Doc. No.: S0167-9317(00)00459-7  
 Published by: Elsevier  
 Price: CCCC 0167-9317/2001/\$20.00  
 CODEN: MIENEF ISSN: 0167-9317  
 SICI: 0167-9317(200103)55:1/4L:291:DTSE;1-W  
 Conference: Fourth European Workshop on Materials for Advanced Metallization. Stresa, Italy, 28 Feb-1 March 2000  
 Sponsor(s): STMicroelectron.; INFM; CNR-Madess  
 DT Conference Article; Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L10 ANSWER 13 OF 24 INSPEC (C) 2005 IEE on STN



AN 2000:6749178 INSPEC DN B2000-12-2550F-086  
 TI Overview of Cu contamination during integration in a dual damascene architecture for sub-quarter micron technology.  
 AU Torres, J.; Palleau, J. (France Telecom, CNET, Meylan, France); Tardif, F.; Bernard, H.; Motte, P.; Pantel, R.; Juhel, M.  
 SO Advanced Metallization Conference in 1998 (AMC 1998). Proceedings of the Conference  
 Editor(s): Sandhu, G.S.; Koerner, H.; Murakami, M.; Yasuda, Y.; Kobaysahi, N.  
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.645-51 of xx+784 pp. 10 refs.  
 Conference: Colorado Springs, CO, USA & Tokyo, Japan, 6-8 Oct 1998 & 3-4 Sept 1998  
 Sponsor(s): Continuing Educ. Eng.; Univ. Extension; Univ. California at Berkeley  
 ISBN: 1-55899-484-X  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 14 OF 24 INSPEC (C) 2005 IEE on STN



AN 2000:6721998 INSPEC DN B2000-11-2550F-052  
 TI Reliability of dual damascene Cu metallization.  
 AU Tsai, M.H.; Tsai, W.J.; Shue, S.L.; Yu, C.H.; Liang, M.S. (Taiwan Semicond. Manuf. Co. Ltd., Hsin-Chu, Taiwan)  
 SO Proceedings of the IEEE 2000 International Interconnect Technology Conference (Cat. No.00EX407)  
 Piscataway, NJ, USA: IEEE, 2000. p.214-16 of 277 pp. 4 refs.  
 Conference: Burlingame, CA, USA, 5-7 June 2000  
 Sponsor(s): IEEE Electron Devices Soc  
 Price: CCCC 0 7803 6327 2/2000/\$10.00  
 ISBN: 0-7803-6327-2  
 DT Conference Article  
 TC Practical  
 CY United States  
 LA English

L10 ANSWER 15 OF 24 INSPEC (C) 2005 IEE on STN



AN 2000:6500494 INSPEC DN A2000-06-8160B-066; B2000-03-2550F-063  
 TI Overview of Cu contamination during integration in a dual damascene architecture for sub-quarter micron technology.  
 AU Torres, J.; Palleau, J. (FT, CNET, Meylan, France); Tardif, F.; Bernard, H.; Beverina, A.; Motte, P.; Pantel, R.; Juhel, M.  
 SO Microelectronic Engineering (Jan. 2000) vol.50, no.1-4, p.425-31. 4 refs.  
 Doc. No.: S0167-9317(99)00311-1  
 Published by: Elsevier  
 Price: CCCC 0167-9317/2000/\$20.00  
 CODEN: MIENEF ISSN: 0167-9317  
 SICI: 0167-9317(200001)50:1/4L.425:OCDI;1-N  
 Conference: Third European Workshop on Materials for Advanced Metallization. Ostende, Belgium, 7-10 March 1999  
 DT Conference Article; Journal  
 TC Experimental

L10 ANSWER 19 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 1999:6123474 INSPEC DN A1999-03-7155-021; B1999-02-2520C-013  
 TI Electrical and recombination properties of copper-silicide precipitates in silicon.  
 AU Istratov, A.A. (Dept. of Mater. Sci. & Miner. Eng., California Univ., Berkeley, CA, USA); Hedemann, H.; Seibt, M.; Vyvenko, O.F.; Schroter, W.; Heiser, T.; Flink, C.; Hieslmair, H.; Weber, E.R.  
 SO Journal of the Electrochemical Society (Nov. 1998) vol.145, no.11, p.3889-98. 52 refs.  
 Published by: Electrochem. Soc  
 Price: CCCC 0013-4651/98/\$7.00  
 CODEN: JESOAN ISSN: 0013-4651  
 SICI: 0013-4651(199811)145:11L:3889:ERPC;1-4  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 20 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 1998:6018767 INSPEC DN A9820-6822-008; B9810-2550F-037  
 TI Barrier properties of very thin Ta and TaN layers against **copper diffusion**.  
 AU Wang, M.T.; Lin, Y.C.; Chen, M.C. (Dept. of Electron. Eng., Nat. Chiao Tung Univ., Hsinchu, Taiwan)  
 SO Journal of the Electrochemical Society (July 1998) vol.145, no.7, p.2538-45. 36 refs.  
 Published by: Electrochem. Soc  
 Price: CCCC 0013-4651/98/\$7.00  
 CODEN: JESOAN ISSN: 0013-4651  
 SICI: 0013-4651(199807)145:7L:2538:BPVT;1-8  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 21 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 1989:3414417 INSPEC DN A89087111  
 TI Formation of the 110-K superconducting phase **via** the amorphous state in the Bi-Sr-Ca-Cu-O system.  
 AU Shi, D.; Tang, M.; Vandervoort, K.; Claus, H. (Div. of Mater. Sci., Argonne Nat. Lab., IL, USA)  
 SO Physical Review B (Condensed Matter) (1 May 1989) vol.39, no.13, p.9091-8. 16 refs.  
 CODEN: PRBMDO ISSN: 0163-1829  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 22 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 1984:2304411 INSPEC DN A84088591; B84046866

TI Stress effect in Au-Si Schottky diode doped with Cu.  
 AU Toyama, N. (Dept. of Electronics, Kyushu Inst. of Technol.,  
 Kitakyushu-shi, Japan)  
 SO Journal of Applied Physics (15 June 1984) vol.55, no.12, p.4398-403. 23  
 refs.  
 Price: CCCC 0021-8979/84/124398-06\$02.40  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L10 ANSWER 23 OF 24 INSPEC (C) 2005 IEE on STN

Full Text  
 Abstract

AN 1980:1484641 INSPEC DN A80034240  
 TI On the rate-controlling step of **copper diffusion**/oxidation through gold.  
 AU Tompkins, H.G.; Pinnel, M.R. (Bell Telephone Lab., Columbus, OH, USA)  
 SO Journal of Applied Physics (Nov. 1979) vol.50, no.11, pt.1, p.7243-4. 5  
 refs.  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Theoretical  
 CY United States  
 LA English

L10 ANSWER 24 OF 24 INSPEC (C) 2005 IEE on STN

Full Text  
 Abstract

AN 1977:1116753 INSPEC DN A77080652; B77041052  
 TI Relative rates of nickel diffusion and **copper diffusion** through gold  
 (electrical contacts applications).  
 AU Tompkins, H.G.; Pinnel, M.R. (Bell Telephone Labs., Columbus, OH, USA)  
 SO Journal of Applied Physics (July 1977) vol.48, no.7, p.3144-6. 15 refs.  
 CODEN: JAPIAU ISSN: 0021-8979  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

=>



Creation date: 07-29-2005  
Indexing Officer: LNGUYEN20 - LOAN NGUYEN  
Team: PUBSImageAssistanceCtr  
Dossier: 10939655

Legal Date: 07-29-2005

No.	Doccode	Number of pages
1	ABN	2

Total number of pages: 2

Remarks:

Order of re-scan issued on .....